



PTO/SB/08A (10-01)

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|---|---|----|---|--------------------------|--------------------|
| Institute for form 1448A/PTO  |   |    |   | <b>Complete if Known</b> |                    |
| <b>INFORMATION DISCLOSURE<br/>STATEMENT BY APPLICANT</b><br><br>(use as many sheets as necessary) |   |    |   | Application Number       | 09/943,199         |
|   |   |    |   | Filing Date              | August 29, 2001    |
|   |   |    |   | First Named Inventor     | Kristy A. Campbell |
|   |   |    |   | Art Unit                 | 2818               |
|   |   |    |   | Examiner Name            | D. Vu              |
| Sheet   | 1 | of | 5 | Attorney Docket Number   | M4065.0704/P704    |

| U.S. PATENT DOCUMENTS |                       |   |                                |  |   |
|-----------------------|-----------------------|---|--------------------------------|--|---|
| Examiner Initials*    | Cite No. <sup>1</sup> | Document Number<br>Number-Kind Code <sup>2</sup> (if known) | Publication Date<br>MM-DD-YYYY | Name of Patentee or<br>Applicant of Cited Document | Pages, Columns, Lines, Where<br>Relevant Passages or Relevant<br>Figures Appear |
| DV                    | AA                    | 2002/000866   | 1/3/2002                       | Kozicki et al.                                     |   |
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|                       | AC                    | 2002/010849   | 08/08/2002                     | Moore  |   |
|                       | AD                    | 2002/0123189  | 09/05/2002                     | Moore et al.                                       |   |
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|                       | AH                    | 2002/0132417  | 09/09/2002                     | Li   |   |
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|                       | AP                    | 2003/0027416  | 02/06/2003                     | Moore  |   |
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|                       | AS                    | 2003/0035315  | 02/20/2003                     | Kozicki  |   |
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|                       | AX                    | 2003/0047765  | 03/13/2003                     | Campbell   |   |
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|                       | AZ                    | 2003/0047773  | 03/13/2003                     | Li   |   |
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**INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT**

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**Complete If Known**

|                        |                    |
|------------------------|--------------------|
| Application Number     | 09/943,199         |
| Filing Date            | August 29, 2001    |
| First Named Inventor   | Kristy A. Campbell |
| Art Unit               | 2818               |
| Examiner Name          | D. Vu              |
| Attorney Docket Number | M4065.0704/P704    |

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|    |     |              |            |                        |  |
|----|-----|--------------|------------|------------------------|--|
| PV | AR1 | 2003/0209971 | 11/13/2003 | Kozicki et al.         |  |
|    | AS1 | 2003/0210564 | 11/13/2003 | Kozicki et al.         |  |
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|    | AU1 | 2003/0212725 | 11/2003    | Ovshinsky et al.       |  |
|    | AV1 | 2004/0035401 | 2/2004     | Ramachandran et al.    |  |
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|    | AC2 | 4,177,474    | 12/1979    | Ovshinsky              |  |
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|    | AE2 | 4,316,946    | 1/1982     | Masters, et al.        |  |
|    | AF2 | 4,597,162    | 7/1986     | Johnson et al.         |  |
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|    | AH2 | 4,637,895    | 1/1987     | Ovshinsky et al.       |  |
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|    | AJ2 | 4,664,939    | 5/1987     | Ovshinsky              |  |
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|    | AX2 | 4,788,594    | 11/1988    | Ovshinsky et al.       |  |
|    | AY2 | 4,800,526    | 01/24/1989 | Lewis                  |  |
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|    | AF3 | 5,128,099    | 7/1992     | Strand et al.          |  |
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|    | AL3 | 5,335,219    | 8/1994     | Ovshinsky et al.       |  |
| Y  | AM3 | 5,341,328    | 8/1994     | Ovshinsky et al.       |  |
| PV | AN3 | 5,359,205    | 10/1994    | Ovshinsky              |  |

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| Examiner Name          | D. Vu              |
| Attorney Docket Number | M4065.0704/P704    |

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|    |     |           |            |                    |  |
|----|-----|-----------|------------|--------------------|--|
| p✓ | AO3 | 5,406,509 | 4/1995     | Ovshinsky et al.   |  |
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|    | AX3 | 5,694,054 | 12/1997    | Ovshinsky et al.   |  |
|    | AY3 | 5,714,768 | 2/1998     | Ovshinsky et al.   |  |
|    | AZ3 | 5,814,527 | 9/29/1998  | Wolstenholme et al |  |
|    | AA4 | 5,818,749 | 10/06/1998 | Harshfield         |  |
|    | AB4 | 5,825,046 | 10/1998    | Czubatyj et al.    |  |
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|    | AD4 | 5,869,843 | 2/9/1999   | Harshfield         |  |
|    | AE4 | 5,912,839 | 6/1999     | Ovshinsky et al.   |  |
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|    | AG4 | 6,011,757 | 1/2000     | Ovshinsky          |  |
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|    | AO4 | 6,437,383 | 8/2002     | Xu                 |  |
|    | AP4 | 6,440,837 | 8/27/2002  | Harshfield         |  |
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|    | AT4 | 6,487,106 | 11/26/2002 | Kozicki            |  |
|    | AU4 | 6,487,113 | 11/2002    | Park et al.        |  |
|    | AV4 | 6,501,111 | 12/2002    | Lowery             |  |
|    | AW4 | 6,507,061 | 1/2003     | Hudgens et al.     |  |
|    | AX4 | 6,511,862 | 1/2003     | Hudgens et al.     |  |
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|    | AB5 | 6,531,373 | 3/2003     | Gill et al.        |  |
|    | AC5 | 6,534,781 | 3/2003     | Dennison           |  |
|    | AD5 | 6,545,287 | 4/2003     | Chiang             |  |
|    | AE5 | 6,545,907 | 4/2003     | Lowery et al.      |  |
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|    | AG5 | 6,563,184 | 5/2003     | Lowery et al.      |  |
|    | AH5 | 6,566,700 | 5/2003     | Xu                 |  |
|    | AI5 | 6,567,293 | 5/2003     | Lowery et al.      |  |
| ✓  | AJ5 | 6,569,705 | 5/2003     | Chiang et al.      |  |
| 0✓ | AK5 | 6,570,784 | 5/2003     | Lowery             |  |

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## Complete If Known

|                        |                    |
|------------------------|--------------------|
| Application Number     | 09/943,189         |
| Filing Date            | August 29, 2001    |
| First Named Inventor   | Kristy A. Campbell |
| Art Unit               | 2818               |
| Examiner Name          | D. Vu              |
| Attorney Docket Number | M4065.0704/P704    |

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|   |     |           |         |                   |  |
|---|-----|-----------|---------|-------------------|--|
| ✓ | AL5 | 6,576,921 | 6/2003  | Lowery            |  |
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|   | AQ5 | 6,597,009 | 7/2003  | Wicker            |  |
|   | AR5 | 6,605,527 | 8/2003  | Dennison et al.   |  |
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|   | AT5 | 6,621,095 | 9/2003  | Chiang et al.     |  |
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|   | AV5 | 6,642,102 | 11/2003 | Xu                |  |
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|   | AX5 | 6,649,928 | 11/2003 | Dennison          |  |
|   | AY5 | 6,687,900 | 12/2003 | Lowery et al.     |  |
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|   | AA8 | 6,673,648 | 1/2004  | Lowrey            |  |
|   | AB6 | 6,673,700 | 1/2004  | Dennison et al.   |  |
|   | AC8 | 6,674,115 | 1/2004  | Hudgens et al.    |  |
|   | AD6 | 6,687,153 | 2/2004  | Lowery            |  |
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| Examiner Initials* | Cite No. <sup>1</sup> | Foreign Patent Document   | Publication Date MM-DD-YYYY | Name of Patentee or Applicant of Cited Document | Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear | † |
|--------------------|-----------------------|---|-----------------------------|---|---|---|
|                    |                       | Country Code <sup>2</sup> -Number <sup>3</sup> -Kind Code <sup>4</sup> (if known) |                             |   |   |   |
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|                    |               |                 |          |
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| Examiner Signature | <i>Shudor</i> | Date Considered | 12/08/04 |
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Sheet 5 of 5

## Complete if Known

|                        |                    |
|------------------------|--------------------|
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| Group Art Unit         | 2818               |
| Examiner Name          | D. Vu              |
| Attorney Docket Number | M4065.0704/P704    |

## OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS

| Examiner Initials | Cite No. <sup>1</sup> | Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published. | T <sup>2</sup> |
|-------------------|-----------------------|--|----------------|
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|                    |                |                 |          |
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| Examiner Signature | <i>Phuland</i> | Date Considered | 12/08/04 |
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\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

<sup>1</sup>Applicant's unique citation designation number (optional). <sup>2</sup>Applicant is to place a check mark here if English language Translation is attached.

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| Sheet | 1 | of | 8 |
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|-----------------------|--------------------------|--|--------------------------------|--|--|
|                       |                          | Number-Kind Code <sup>2</sup> (if known) |                                |  |  |
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|                       | AF                       | US 2002/0000666                          | 01/03/2002                     | Kozicki et al.                                     |  |
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| DV                    | BA                       | WO 97/488032  | 12/18/1997                     | Kozicki et al.                                     |  |                |
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